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*EXAMINER: Initial identerance considered, whether or not citation is in conformance with MPEP 609. Onew line through citation if not in conformance and not considered fundate copy of this form with next communication to applicant.

1Unique citation designation number. *See attached Kinds of U.S. Patent Documents. *Senter Office that issued the document, by the two-letter code (WIPO Standard St.3). *For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5kGnd of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. *Bapplicant is to place a check mark here if English language Translation is attached.

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| | | | | Application Number | 00/510,802 |
| | INFORMATION DISCL | | | Filing Date | February 23, 2000 |
| l | STATEMENT BY APP | LIC | ANT | First Named Inventor | Herr, Daniel Joseph Christian |
| | | | | Group Art Unit | 2815 |
| | (use as many sheets as ne | 0558 | 72) | Examiner Name | Jackson |
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| | STATEMENT BY API | LIC | ANT | First Named Inventor | Herr, Daniel Joseph Christian | |
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| | (use as many sheets as ne | cesse | n/t | Examiner Name | Jackson | |
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